

KLB-16AI-88

The KLB-16I-88 is GaAlAs infrared emitting diode and has the optimized optical characteristics.

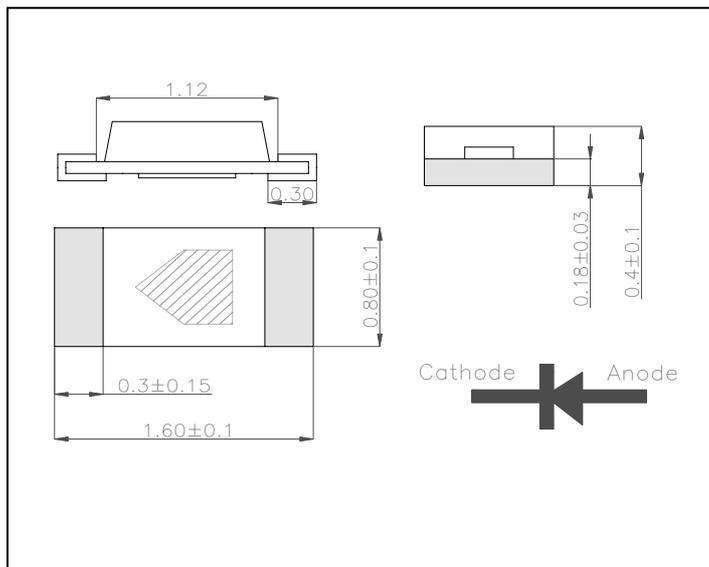
Features

- Ultra Wide Viewing Angle
- 880nm wavelength
- Low forward voltage

Applications

- Display
- Indicator
- Key Pad Back Light
- Car CCD Camera

DIMENSIONS



Maximum Ratings

[Ta=25°C]

Parameter	Symbol	Ratings	Unit
Reverse Voltage	V_R	5	V
Forward current	I_F	50	mA
Pulse forward current *1	I_{FP}	0.7	A
Power dissipation	P_D	75	mW
Operating temperature	$T_{opr.}$	-20 ~ +85	°C
Storage temperature	$T_{stg.}$	-30 ~ +100	°C
Soldering Temperature *2	$T_{sol.}$	260	°C

*1. I_{FP} Measured under duty $\leq 1/10$ @ 1KHz

*2. Soldering time ≤ 5 Sec

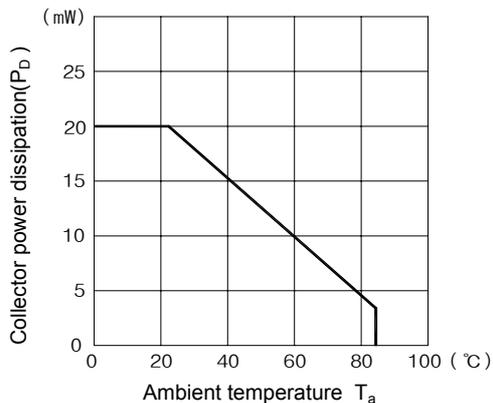
Electro-Optical Characteristics

[Ta=25°C]

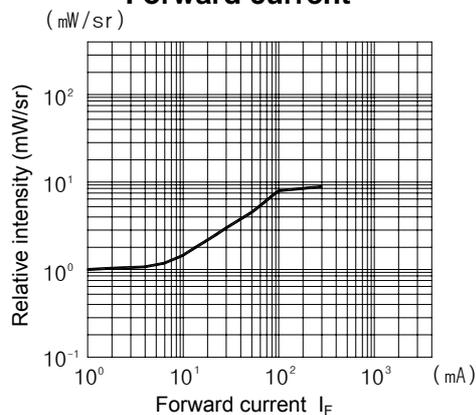
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 20$ mA	-	1.30	1.5	V
Reverse current	IR	$V_R = 5$ V	-	-	10	μ A
Radiant intensity	I_e	$I_F = 20$ mA	1.0	1.5	-	mW/sr
Radiant Power	P_o	$I_F = 20$ mA	-	1.3	-	mW
Peak emission wavelength	λ_p	$I_F = 20$ mA	-	880	-	nm
Spectral bandwidth	$\Delta\lambda$	$I_F = 20$ mA	-	45	-	nm
Half angle	$\Delta\theta$	$I_F = 20$ mA	-	160	-	deg.

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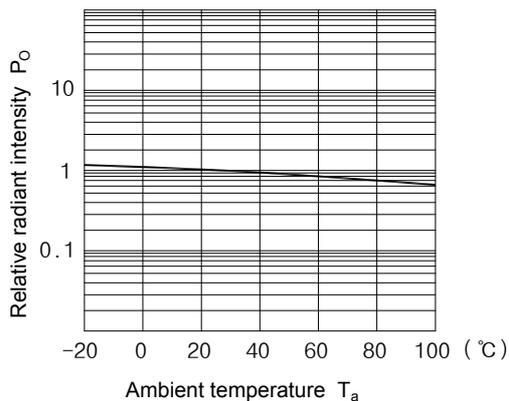
Collector power dissipation Vs Ambient temperature



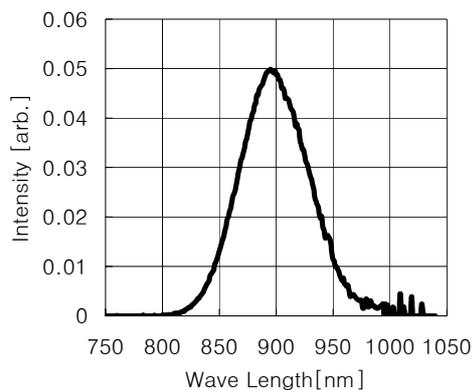
Radiant Intensity vs. Forward current



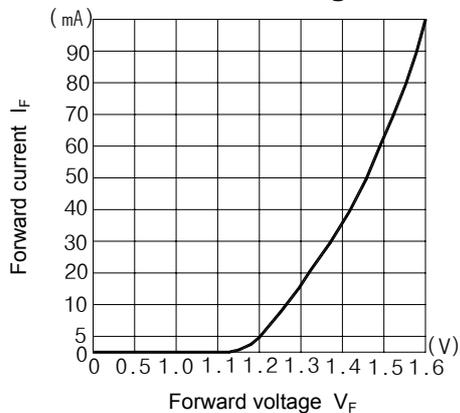
Relative radiant intensity vs. Ambient temperature



Relative intensity vs. Wavelength



Forward current vs. Forward voltage



Radiant Pattern

